Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note: Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp. Customer Support Dept. April 1, 2003



Description

The M16C/62M (80-pin version) group (low voltage version) of single-chip microcomputers are built using the high-performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 80-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, they are capable of executing instructions at high speed. They also feature a built-in multiplier and DMAC, making them ideal for controlling office, communications, industrial equipment, and other high-speed processing applications. The M16C/62M (80-pin version) group (low voltage version) includes a wide range of products with different internal memory types and sizes and various package types.

Features

Memory capacity	ROM (See Figure 1.1.3. ROM Expansion) RAM 10K to 20K bytes
• Shortest instruction execution time	100ns (f(XIN)=10MHz, Vcc=2.7V to 3.6V)
	142.9ns (f(XIN)=7MHz, VCC=2.2V to 3.6V, with software one-wait)
Supply voltage	2.7V to 3.6V (f(XIN)=10MHz, without software wait)
	2.4V to 2.7V (f(XIN)= 7MHz, without software wait)
	2.2V to 2.4V (f(XIN)= 7MHz, with software one-wait)
Low power consumption	28.5mW (f(XIN)=10MHz, with software one-wait, VCC = 3V)
Interrupts	25 internal and 5 external interrupt sources, 4 software
	interrupt sources; 7 levels (including key input interrupt)
Multifunction 16-bit timer	5 output timers + 6 input timers (3 for timer function only)
• Serial I/O	5 channels (2 for UART or clock synchronous, 1 for UART, 2 for clock synchronous)
• DMAC	2 channels (trigger: 24 sources)
A-D converter	10 bits X 8 channels (Expandable up to 10 channels)
D-A converter	8 bits X 2 channels
CRC calculation circuit	1 circuit
Watchdog timer	
Programmable I/O	
Input port	
Clock generating circuit	2 built-in clock generation circuits
	(built-in feedback resistor, and external ceramic or quartz oscillator)

Note: Memory expansion mode and microprocessor mode are not supported.

Applications

Audio, cameras, office equipment, communications equipment, portable equipment



Pin Configuration

Figures 1.1.1 show the pin configurations (top view).

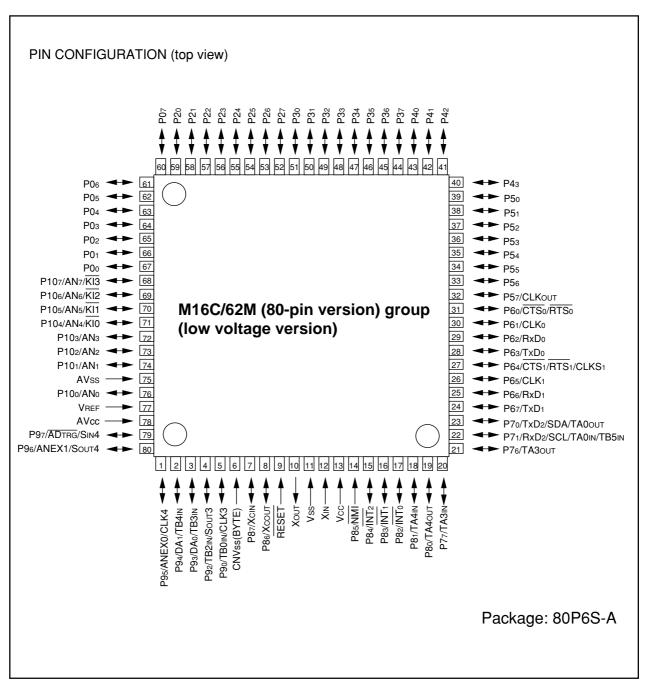


Figure 1.1.1. Pin configuration (top view)

Block Diagram

Figure 1.1.2 is a block diagram of the M16C/62M (80-pin version) group (low voltage version).

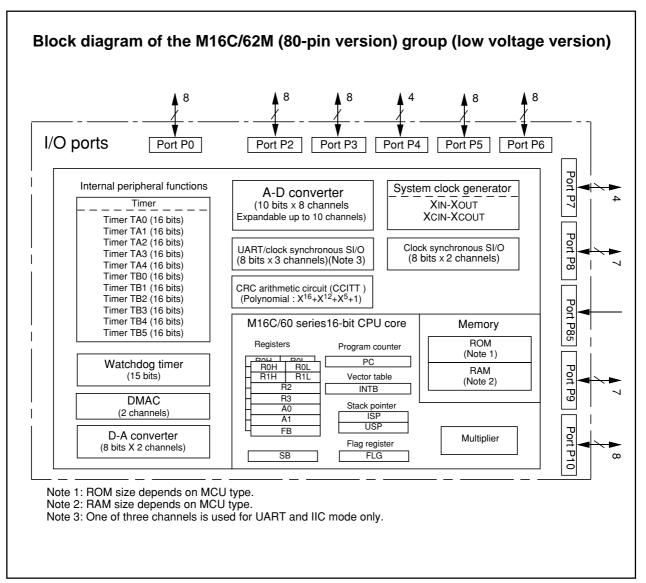


Figure 1.1.2. Block diagram of M16C/62M (80-pin version) group (low voltage version)

Performance Outline

Table 1.1.1 is a performance outline of M16C/62M (80-pin version) group (low voltage version).

Table 1.1.1. Performance outline of M16C/62M (80-pin version) group (low voltage version)

	Item	Performance				
Number of ba	sic instructions	91 instructions				
Shortest instru	uction execution time	100ns(f(XIN)=10MHz, VCC=2.7V to 3.6V)				
		142.9ns (f(XIN)=7MHz, VCC=2.2V to 3.6V, with software one-				
		wait)				
Memory	ROM	(See the figure 1.1.3. ROM Expansion)				
capacity	RAM	10K to 20K bytes				
I/O port	P0 to P10 (except P85)	8 bits x 6, 7 bits x 2, 4 bits x 2				
Input port	P85	1 bit x 1				
Multifunction	TA0, TA3, TA4	16 bits x 3 (timer mode, internal/external event count,				
timer		one-shot timer mode and pulse width measurement mode)				
TB0, TB2, TB3, TB4, TB5		16 bits x 5 (timer mode, internal/external event count				
		and pulse period/pulse width measurement mode)				
	TA1, TA2	16 bits x 2 (timer mode, internal event count and				
		a trigger through one-shot timer mode occurs.)				
	TB1	16 bits x 1 (timer mode and internal event count)				
Serial I/O	UART0, UART1, UART2	(UART or clock synchronous) x 2, UART x 1(UART2)				
	SI/O3, SI/O4	(Clock synchronous) x 2 (SI/O3 is output only)				
A-D converter		10 bits x (8 + 2) channels				
D-A converter		8 bits x 2				
DMAC		2 channels (trigger: 24 sources)				
CRC calculation	on circuit	CRC-CCITT				
Watchdog tim	er	15 bits x 1 (with prescaler)				
Interrupt		25 internal and 5 external sources, 4 software sources, 7 levels				
Clock generat	ing circuit	2 built-in clock generation circuits				
		(built-in feedback resistor, and external ceramic or quartz oscillator)				
Supply voltage	е	2.7V to 3.6V (f(XIN)=10MHz, without software wait)				
		2.4V to 2.7V (f(XIN)= 7MHz, without software wait)				
		2.2V to 2.4V (f(XIN)= 7MHz, with software one-wait)				
Power consur	nption	28.5mW (f(XIN) = 10MHz, Vcc=3V with software one-wait)				
I/O	I/O withstand voltage	3V				
	Output current	1mA				
Device config	uration	CMOS high performance silicon gate				
Package		80-pin plastic mold QFP				

Note: M16C/62M (80-pin version) group (low voltage version) does not support memory expansion or microprocessor mode.



Mitsubishi plans to release the following products in the M16C/62M (80-pin version) group (low voltage version):

- (1) Support for mask ROM version and flash memory version
- (2) ROM capacity
- (3) Package

80P6S-A : Plastic molded QFP (mask ROM and flash memory versions)

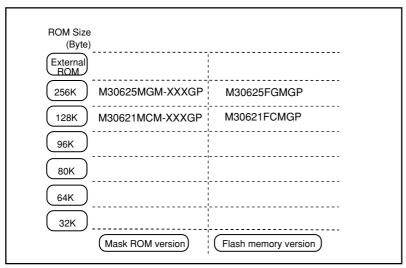


Figure 1.1.3. ROM expansion

The M16C/62M (80-pin version) group (low voltage version) products currently supported are listed in Table 1.1.2.

Table 1.1.2. M16C/62M (80-pin version) group (low voltage version)

As of April 2002

				710 01 710111 2002
Type No	ROM capacity	RAM capacity	Package type	Remarks
M30621MCM-XXXGP	128 Kbytes	10 Kbytes	80P6S-A	mask ROM version
M30625MGM-XXXGP	256 Kbytes	20 Kbytes	80P6S-A	mask now version
M30621FCMGP	128 Kbytes	10 Kbytes	80P6S-A	Floor moment 2)/ version
M30625FGMGP	256 Kbytes	20 Kbytes	80P6S-A	Flash memory 3V version

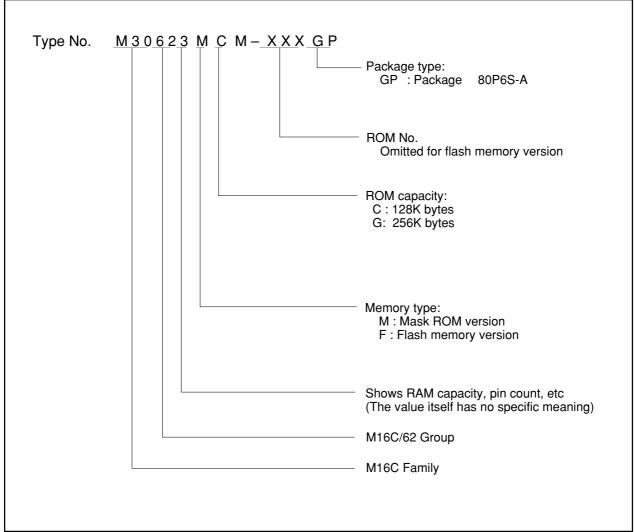


Figure 1.1.4. Type No., memory size, and package

About the M16C/62M (80-pin version) group (low voltage version)

The M16C/62M (80-pin version) group (low voltage version) is packaged in a 80-pin plastic mold package. The number of pins in comparison with the 100-pin package products is decreased. So be careful about the following.

- (a) The M16C/62M (80-pin version) group (low voltage version) supports single chip mode alone. It supports neither memory expansion mode nor microprocessor mode.
- (b) The input/output ports given below are absent from the M16C/62M (80-pin version) group (low voltage version). To stabilize the internal state, set to output mode the direction register of each input/output port. Failing in setting to output mode involves an increase in current consumption.

<Pins absent from the 80-pin version> P10 to P17, P44 to P47, P72 to P75, P91

- (c) INT3 to INT5 allocated to P15 to P17 cannot be used. Keep the INT3 interrupt control register disabled for interrupts. The INT4 interrupt control register and the INT5 interrupt control register are shared with SI/O3 and SI/O4. When the user don't use them as SI/O3 and SI/4, set them disabled for interrupts.
- (d) The output pins of timers A1 and A2 TA1IN, TA1OUT, TA2IN and TA2OUT allocated to P72 to P75 cannot be used. In connection with this, the gate function and pulse outputting function of timers A1 and A2 cannot be used. Use timer mode and internal event count, or use as trigger signal generation in one-shot timer mode.
- (e) The UART2 input/output pins CLK2 and CTS/RTS allocated to P72 and P73 cannot be used. In connection with this, UART2 solely as UART of the internal clock can be used.
- (f) The input pin TB1IN of timer B1 allocated to P91 cannot be used. With timer B1 under this state, use only timer mode or the internal event count.
- (g) The input pin SIN3 of serial I/O3 allocated to P91 cannot be used. In connection with this, use serial I/O3 as a serial I/O exclusive to transmission.
- (h) The output pins for three-phase motor control allocated to P72 to P75 cannot be used. So set to 0 (ordinary mode) the mode select bit (bit 2) of three-phase PWM control register 0.



Table 1.20.1. Absolute maximum ratings

Symbol		Parameter	Condition	Rated value	Unit
Vcc	Supply volta	Supply voltage		-0.3 to 4.6	V
AVcc	Analog supply voltage		Vcc=AVcc	-0.3 to 4.6	V
Vı	Input voltage	RESET, CNVss (BYTE) P00 to P07, P20 to P27, P30 to P37, P40 to P43, P50 to P57, P60 to P67, P76 to P77, P80 to P87, P90, P92 to P97, P100 to P107, VREF, XIN		-0.3 to Vcc+0.3	V
		P70, P71		-0.3 to 4.6	V
Vo	Output voltage	P00 to P07, P20 to P27, P30 to P37,P40 to P43, P50 to P57, P60 to P67,P76 to P77, P80 to P84, P86, P87, P90, P92 to P97, P100 to P107, XOUT		-0.3 to Vcc+0.3	V
		P70, P71		-0.3 to 4.6	V
Pd	Power dissipation		Ta=25 °C	300	mW
Topr	Operating ambient temperature			-20 to 85 / -40 to 85(Note)	°C
Tstg	Storage tem	nperature		-65 to 150	°C

Note: Specify a product of -40 to 85°C to use it.



Table 1.20.2. Recommended operating conditions (referenced to Vcc = 2.2V to 3.6V at Ta = -20° C to 85°C (-40° C to 85°C (Note3) unless otherwise specified)

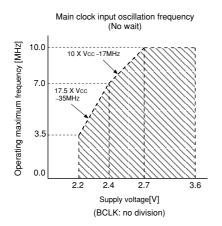
			St					
Symbol			Paramet	er	Min.	Тур.	Max. 3.6 Vcc 4.6 0.2Vcc -10.0 -5.0 10.0	Unit
Vcc	Supply voltage	ge			2.2	3.0	3.6	V
AVcc	Analog suppl	ly voltage				Vcc		V
Vss	Supply voltage	ge				0		V
AVss	Analog suppl	g supply voltage				0		V
VIH	HIGH input voltage P00 to P07, P20 to P27, P30 to P37, P40 to P43, P50 to P57, P60 to P67, P76, P77, P80 to P87, P90, P92 to P97, P100 to P107, XIN, RESET, CNVss (BYTE)				0.8Vcc		Vcc	٧
	P70, P71				0.8Vcc		4.6	V
VIL	LOW input voltage	P40 to P P80 to P	07, P20 to P27, P30 43, P50 to P57, P60 87, P90, P92 to P97 SET, CNVss (BYTE	to P67, P70, P71,P76, P77, r, P100 to P107,	0		0.2Vcc	V
	LUCII post s		, ,	,				
I _{OH (peak)}	HIGH peak output current P00 to P07, P20 to P27,P30 to P37, P40 to P43, P50 to P57, P60 to P67, P76, P77, P80 to P84, P86, P87, P90, P92 to P97, P100 to			P57, P60 to P67, P76, P77,			-10.0	mA
I OH (avg)	HIGH average output P00 to P07, P20 to P27, P30 to P37, current P40 to P43, P50 to P57, P60 to P67, P76, P77,			P57, P60 to P67, P76, P77,			-5.0	mA
I _{OL (peak)}	P80 to P84, P86, P87, P90, P92 to P97, P100 to P107 LOW peak output current P00 to P07, P20 to P27,P30 to P37, P40 to P43, P50 to P57, P60 to P67, P70, P71, P76, P7980 to P84, P86, P87, P90, P92 to P97, P100 to P107			P27,P30 to P37, P57, P60 to P67, P70, P71, P76, P77			10.0	mA
I _{OL} (avg)	LOW average output curren	nt		P27,P30 to P37, P57, P60 to P67, P70, P71, P76, P77 B7, P90, P92 to P97, P100 to P107			5.0	mA
			·	Vcc=2.7V to 3.6V	0		10	MHz
£ (V)	Main clock input oscillation frequency (Note 5)		No wait	Vcc=2.4V to 2.7V	0		10 X Vcc -17	MHz
f (XIN)				Vcc=2.2V to 2.4V	0		17.5 X Vcc -35	MHz
				Vcc=2.7V to 3.6V	0		10	MHz
	with		with wait	Vcc=2.2V to 2.7V	0		6 X Vcc -6.2	MHz
f (Xcin)	Subclock osc	cillation fro	auency			32.768	50	kHz

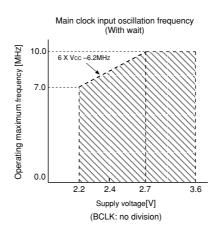
Note 1: The mean output current is the mean value within 100ms.

Note 2: The total IOL (peak) for all ports must be 80mA max. The total IOH (peak) for all ports must be 80mA max.

Note 3: Specify a product of -40°C to 85°C to use it.

Note 4: Relationship between main clock oscillation frequency and supply voltage.





Flash memory version program voltage and read operation voltage characteristics

Flash program voltage	Flash read operation voltage
Vcc=2.7V to 3.6V	Vcc=2.4V to 3.6V
Voc2 7V to 2 4V	Voc-2 2V to 2 4V

Note 5: Execute case without wait, program / erase of flash memory by Vcc=2.7V to 3.6V and $f(BCLK) \le 6.25$ MHz. Execute case with wait, program / erase of flash memory by Vcc=2.7V to 3.6V and $f(BCLK) \le 10.0$ MHz.

Table 1.20.3. A-D conversion characteristics (referenced to VCC = AVCC = VREF = 2.4V to 3.6V, VSS = AVSS = 0V at Ta = -20°C to 85°C / -40°C to 85°C(Note2), f(XIN) = 10MHz unless otherwise specified)

Cumphal	Davianiata	Manageria and distant	S	I Inch		
Symbol	Parameter	Measuring condition	Min.	Тур.	Max	Unit
-	Resolution	VREF = VCC			10	Bits
-	Absolute accuracy, sample & hold function not available (8 bit)	VREF = VCC = 3V, ϕ AD = $f(Xin)/2$			±2	LSB
RLADDER	Ladder resistance	VREF = VCC	10		40	kΩ
tconv	Conversion time(8bit), sample & hold function not available	$V_{REF} = V_{CC} = 3V$, $\phi_{AD} = f(X_{IN}) = f_{AD}/2 = 5MHz$	9.8		Vcc	μs
tsamp	Sampling time		0.3			μs
VREF	Reference voltage		2.4		Vcc	٧
VIA	Analog input voltage		0		VREF	V

Note 1: Connect AV cc pin to Vcc pin and apply the same electric potential.

Note 2: Specify a product of -40°C to 85°C to use it.

Table 1.20.4. D-A conversion characteristics (referenced to VCC = 2.4V to 3.6V, VSS = AVSS = 0V, VREF = 3V, at Ta = -20° C to 85° C (-40° C to 85° C(Note2), f(XIN) = 10MHz unless otherwise specified)

Courselle sel	D	NA	5	11.21		
Symbol	Parameter	Measuring condition	Min.	Тур.	Max.	Unit
_	Resolution				8	Bits
_	Absolute accuracy				1.0	%
tsu	Setup time				3	μs
Ro	Output resistance		4	10	20	kΩ
IVREF	Reference power supply input current	(Note)			1.5	mA

Note 1: This applies when using one D-A converter, with the D-A register for the unused D-A converter set to "0016"

The A-D converter's ladder resistance is not included.

Also, when DA register contents are not "00", the current I VREF always flows even though Vref may have been set to be unconnected by the A-D control register.

Note 2: Specify a product of -40°C to 85°C to use it.

Table 1.20.5. Flash memory version electrical characteristics

(referenced to Vcc = 2.7V to 3.6V, at Ta =0°C to 60°C unless otherwise specified)

Parameter		Standard				
Parameter	Min.	Typ.	Max	Unit		
Page program time		6	120	ms		
Block erase time		50	600	ms		
Erase all unlocked blocks time		50 X n (Note)	600 X n (Note)	ms		
Lock bit program time		6	120	ms		

Note: n denotes the number of block erases.

Table 1.20.6. Flash memory version program voltage and read operation voltage characteristics ($Ta = 0^{\circ}C$ to $60^{\circ}C$)

Flash program voltage	Flash read operation voltage
Vcc=2.7V to 3.6V	Vcc=2.4V to 3.6V
Vcc=2.7V to 3.4V	Vcc=2.2V to 2.4V



Table 1.20.7. Electrical characteristics (referenced to VCC = 2.7V to 3.6V, VSS = 0V at $Ta = -20^{\circ}C$ to 85°C / - 40°C to 85°C(Note 1), f(XIN) = 10MHz without wait unless otherwise specified)

Symbol		Parameter		Measuring cond	ition		Standar		Unit
5,001				sasaring cond		Min.	Тур.	Max.	5111
Vон	HIGH output voltage	P00 to P07, P20 to P27, P40 to P43, P50 to P57, P76, P77, P80 to P84, P P90, P92 to P97, P100 t	P60 to P67, 86, P87,	Іон=–1 mA	Іон= –1mA				V
	HIGH output	Your	HIGHPOWER	Iон=-0.1mA		2.5			
Vон	voltage	X001	LOWPOWER	Іон=–50μΑ		2.5			V
	HIGH output	Vacut	HIGHPOWER	With no load applied			3.0		v
	voltage	XCOUT	LOWPOWER	With no load applied			1.6		١ '
VoL	LOW output voltage	P00 to P07, P20 to P27, P40 to P43, P50 to P57, P70, P71, P76, P77, P80 P87, P90, P92 to P97, P	P60 to P67, to P84, P86,	IoL=1mA				0.5	v
Vol	LOW output	Хоит	HIGHPOWER	IoL=0.1mA				0.5	v
VOL	voltage	7,001	LOWPOWER	IoL=50μA				0.5] "
	LOW output	YCOUT	HIGHPOWER	With no load applied			0		v
	voltage	X0001	LOWPOWER	With no load applied			0		1 "
VT+-VT-	Hysteresis	TA0IN, TA3IN, TA4IN, TB0IN, TB2IN to TB5IN, I ADTRG,CTS0,CTS1 CLK CLK4, TA3OUT, TA4OUT, SIN4, RxD0 to RxD2	(o,CLK1,CLK3,		wiii по юдо аррiied			0.8	V
VT+-VT-	Hysteresis	RESET				0.2		1.8	V
Іін	HIGH input current	P00 to P07, P20 to P27, P40 to P43, P50 to P57, P70, P71, P76, P77, P80 P90, P92 to P97, P100 t XIN, RESET, CNVss (B	P60 to P67, to P87, o P107,	Vi=3V				4.0	μА
I _{IL}	LOW input current	P00 to P07, P20 to P27, P40 to P43, P50 to P57, P70, P71, P76, P77, P80 P90, P92 to P97, P100 t XIN, RESET, CNVss (B	P60 to P67, to P87, o P107,	Vi=0V				-4.0	μА
R _{PULLUP}	Pull-up resistance	P00 to P07, P20 to P27, P40 to P43, P50 to P57, P76, P77, P80 to P84, P P90, P92 to P97, P100 t	P60 to P67, 286,P87,	Vi=0V		20	75	300	ΚΩ
R _{fXIN}	Feedback re	sistance XIN					3.0		МΩ
R _{fXCIN}	Feedback re	sistance XCIN					10.0		МΩ
V _{RAM}	RAM retention	on voltage		When clock is stoppe	ed	2.0			V
			The output pins are open and	Mask ROM version	f(X _{IN})=10MHz Square wave, no division		9.5	21.25	mA
			other pins are Vss	Flash memory 3V version	f(XIN)=10MHz Square wave, no division		12.0	21.25	mA
				Mask ROM version Flash memory 3V version	f(XCIN)=32kHz Square wave		45.0		μА
				Flash memory 3V version Program	f(XIN)=10MHz Square wave, division by 2		14.0		mA
				Flash memory 3V version Erase	f(XIN)=10MHz Square wave, division by 2		17.0		mA
Icc	Power supp	ly current		Mask ROM version Flash memory 3V version	f(XCIN)=32kHz When a WAIT instruction is executed. Oscillation capacity High (Note2)		2.8		μА
					f(XCIN)=32kHz When a WAIT instruction is executed. Oscillation capacity Low (Note2)		0.9		μА
					Ta=25°C when clock is stopped			1.0	. μΑ
					Ta=85°C			20.0	'

Note 1: Specify a product of -40°C to 85°C to use it. Note 2: With one timer operated using fC32.



Timing requirements (referenced to VCC = 3V, VSS = 0V at Ta = -20°C to 85°C / - 40°C to 85°C (*) unless otherwise specified)

 * : Specify a product of -40°C to 85°C to use it.

Table 1.20.8. External clock input

Cumbal	Parameter		Standard		
Symbol			Max.	Unit	
tc	External clock input cycle time	100		ns	
tw(H)	External clock input HIGH pulse width	40		ns	
tw(L)	External clock input LOW pulse width	40		ns	
tr	External clock rise time		18	ns	
tf	External clock fall time		18	ns	



Timing requirements (referenced to VCC = 3V, VSS = 0V at Ta = -20° C to 85°C / -40° C to 85°C (*) unless otherwise specified)

* : Specify a product of -40°C to 85°C to use it.

Table 1.20.9. Timer A input (counter input in event counter mode)

Symbol	Parameter	Stand	dard	Unit
Syllibol	Symbol	Min.	Max.	UIIIL
tc(TA)	TAin input cycle time	150		ns
tw(TAH)	TAin input HIGH pulse width	60		ns
tw(TAL)	TAin input LOW pulse width	60		ns

Table 1.20.10. Timer A input (gating input in timer mode)

Symbol	Parameter	Star	ıdard	Unit
Syllibol	Falanetei	Min.	Max.	1 Offic
tc(TA)	TAin input cycle time	600		ns
tw(TAH)	TAin input HIGH pulse width	300		ns
tw(TAL)	TAin input LOW pulse width	300		ns

Table 1.20.11. Timer A input (external trigger input in one-shot timer mode)

Symbol	Davameter	Standard Min. Ma	ndard	l lmit
	Parameter		Max.	Unit
tc(TA)	TAin input cycle time	300		ns
tw(TAH)	TAin input HIGH pulse width	150		ns
tw(TAL)	TAin input LOW pulse width	150		ns

Table 1.20.12. Timer A input (external trigger input in pulse width modulation mode)

Coursels al	Davasatas	Stan	ndard	1.114
Symbol	Parameter	Min.	Max.	Unit
tw(TAH)	TAin input HIGH pulse width	150		ns
tw(TAL)	TAin input LOW pulse width	150		ns

Table 1.20.13. Timer A input (up/down input in event counter mode)

Cumbal	Parameter	Stand	ndard	Unit
Symbol	Farameter	Min.	Max.	UIIIL
tc(UP)	TAiout input cycle time	3000		ns
tw(UPH)	TAiout input HIGH pulse width	1500		ns
tw(UPL)	TAiout input LOW pulse width	1500		ns
tsu(UP-TIN)	TAiout input setup time	600		ns
th(TIN-UP)	TAiout input hold time	600		ns



Timing requirements (referenced to VCC = 3V, Vss = 0V at Ta = -20° C to 85°C / -40° C to 85°C (*) unless otherwise specified)

* : Specify a product of -40°C to 85°C to use it.

Table 1.20.14. Timer B input (counter input in event counter mode)

Cumbal	Parameter	Stand	ndard	Unit
Symbol	r arameter	Min.	Max.	Uniit
tc(TB)	TBin input cycle time (counted on one edge)	150		ns
tw(TBH)	TBiin input HIGH pulse width (counted on one edge)	60		ns
tw(TBL)	TBin input LOW pulse width (counted on one edge)	60		ns
tc(TB)	TBiเห input cycle time (counted on both edges)	300		ns
tw(TBH)	TBin input HIGH pulse width (counted on both edges)	160		ns
tw(TBL)	TBin input LOW pulse width (counted on both edges)	160		ns

Table 1.20.15. Timer B input (pulse period measurement mode)

Symbol	Parameter	Stand	dard	Unit
Symbol	i alametei	Min.	Max.	Offic
tc(TB)	TBin input cycle time	600		ns
tw(TBH)	TBiin input HIGH pulse width	300		ns
tw(TBL)	TBin input LOW pulse width	300		ns

Table 1.20.16. Timer B input (pulse width measurement mode)

Symbol	Parameter	Standard		Unit
Cymbol	i diameter	Min.	Max.	
tc(TB)	TBin input cycle time	600		ns
tw(TBH)	TBiin input HIGH pulse width	300		ns
tw(TBL)	TBiin input LOW pulse width	300		ns

Table 1.20.17. A-D trigger input

Symbol	Parameter	Stand	dard	Unit
Cymbo.	r dramotor	Min.	Max.	Omi
tc(AD)	ADTRG input cycle time (trigger able minimum)	1500		ns
tw(ADL)	ADTRG input LOW pulse width	200		ns

Table 1.20.18. Serial I/O

Symbol	Parameter	Stan	dard	Unit
Symbol	i alametei	Min.	Max.	
tc(CK)	CLKi input cycle time	300		ns
tw(CKH)	CLKi input HIGH pulse width	150		ns
tw(CKL)	CLKi input LOW pulse width	150		ns
td(C-Q)	TxDi output delay time		160	ns
th(C-Q)	TxDi hold time	0		ns
tsu(D-C)	RxDi input setup time	50		ns
th(C-D)	RxDi input hold time	90		ns

Table 1.20.19. External interrupt INTi inputs

	Symbol	pl Parameter	Standard		Unit
l	Symbol	i didilicici	Min.	Max.	Offic
	tw(INH)	INTi input HIGH pulse width	380		ns
I	tw(INL)	INTi input LOW pulse width	380		ns



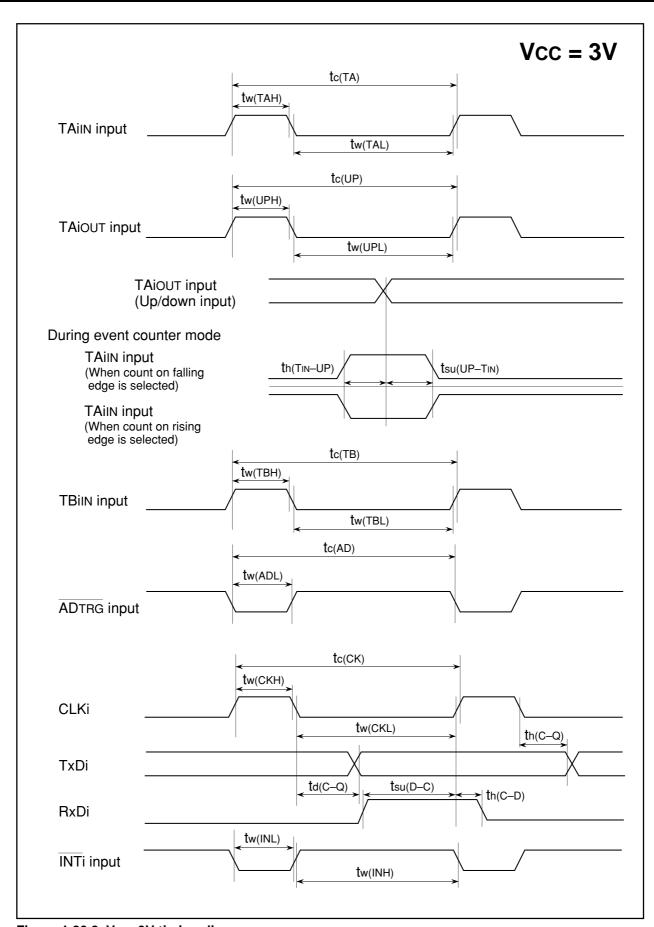


Figure 1.20.2. Vcc=3V timing diagram

Usage Precaution

Timer A (timer mode)

(1) Reading the timer Ai register while a count is in progress allows reading, with arbitrary timing, the value of the counter. Reading the timer Ai register with the reload timing gets "FFFF16". Reading the timer Ai register after setting a value in the timer Ai register with a count halted but before the counter starts counting gets a proper value.

Timer A (event counter mode)

- (1) Reading the timer Ai register while a count is in progress allows reading, with arbitrary timing, the value of the counter. Reading the timer Ai register with the reload timing gets "FFF16" by underflow or "000016" by overflow. Reading the timer Ai register after setting a value in the timer Ai register with a count halted but before the counter starts counting gets a proper value.
- (2) When stop counting in free run type, set timer again.

Timer A (one-shot timer mode)

- (1) Setting the count start flag to "0" while a count is in progress causes as follows:
 - The counter stops counting and a content of reload register is reloaded.
 - The TAiout pin outputs "L" level.
 - The interrupt request generated and the timer Ai interrupt request bit goes to "1".
- (2) The timer Ai interrupt request bit goes to "1" if the timer's operation mode is set using any of the following procedures:
 - Selecting one-shot timer mode after reset.
 - Changing operation mode from timer mode to one-shot timer mode.
 - Changing operation mode from event counter mode to one-shot timer mode.

 Therefore, to use timer Ai interrupt (interrupt request bit), set timer Ai interrupt request bit to "0" after the above listed changes have been made.

Timer A (pulse width modulation mode)

- (1) The timer Ai interrupt request bit becomes "1" if setting operation mode of the timer in compliance with any of the following procedures:
 - · Selecting PWM mode after reset.
 - Changing operation mode from timer mode to PWM mode.
 - Changing operation mode from event counter mode to PWM mode.

Therefore, to use timer Ai interrupt (interrupt request bit), set timer Ai interrupt request bit to "0" after the above listed changes have been made.

(2) Setting the count start flag to "0" while PWM pulses are being output causes the counter to stop counting. If the TAiout pin is outputting an "H" level in this instance, the output level goes to "L", and the timer Ai interrupt request bit goes to "1". If the TAiout pin is outputting an "L" level in this instance, the level does not change, and the timer Ai interrupt request bit does not becomes "1".

Timer B (timer mode, event counter mode)

(1) Reading the timer Bi register while a count is in progress allows reading, with arbitrary timing, the value of the counter. Reading the timer Bi register with the reload timing gets "FFFF16". Reading the timer Bi register after setting a value in the timer Bi register with a count halted but before the counter starts counting gets a proper value.



Timer B (pulse period/pulse width measurement mode)

- (1) If changing the measurement mode select bit is set after a count is started, the timer Bi interrupt request bit goes to "1".
- (2) When the first effective edge is input after a count is started, an indeterminate value is transferred to the reload register. At this time, timer Bi interrupt request is not generated.

A-D Converter

- (1) Write to each bit (except bit 6) of A-D control register 0, to each bit of A-D control register 1, and to bit 0 of A-D control register 2 when A-D conversion is stopped (before a trigger occurs). In particular, when the Vref connection bit is changed from "0" to "1", start A-D conversion after an
- (2) When changing A-D operation mode, select analog input pin again.
- (3) Using one-shot mode or single sweep mode

 Read the correspondence A-D register after confirming A-D conversion is finished. (It is known by A-D conversion interrupt request bit.)
- (4) Using repeat mode, repeat sweep mode 0 or repeat sweep mode 1 Use the undivided main clock as the internal CPU clock.

Stop Mode and Wait Mode

elapse of 1 µs or longer.

- (1) When returning from stop mode by hardware reset, RESET pin must be set to "L" level until main clock oscillation is stabilized.
- (2) When switching to either wait mode or stop mode, instructions occupying four bytes either from the WAIT instruction or from the instruction that sets the every-clock stop bit to "1" within the instruction queue are prefetched and then the program stops. So put at least four NOPs in succession either to the WAIT instruction or to the instruction that sets the every-clock stop bit to "1".

Interrupts

- (1) Reading address 0000016
 - When maskable interrupt is occurred, CPU read the interrupt information (the interrupt number and interrupt request level) in the interrupt sequence.
 - The interrupt request bit of the certain interrupt written in address 0000016 will then be set to "0". Reading address 0000016 by software sets enabled highest priority interrupt source request bit to "0". Though the interrupt is generated, the interrupt routine may not be executed.
 - Do not read address 0000016 by software.
- (2) Setting the stack pointer
 - The value of the stack pointer immediately after reset is initialized to 000016. Accepting an interrupt before setting a value in the stack pointer may become a factor of runaway. Be sure to set a value in the stack pointer before accepting an interrupt.
 - When using the $\overline{\text{NMI}}$ interrupt, initialize the stack point at the beginning of a program. Concerning the first instruction immediately after reset, generating any interrupts including the $\overline{\text{NMI}}$ interrupt is prohibited.
- (3) The NMI interrupt
 - The NMI interrupt can not be disabled. Be sure to connect NMI pin to Vcc via a pull-up resistor if unused.
 - Do not get either into stop mode with the NMI pin set to "L".



- (4) External interrupt
 - When the polarity of the INT0 to INT2 pins is changed, the interrupt request bit is sometimes set to "1". After changing the polarity, set the interrupt request bit to "0".
- (5) Rewrite the interrupt control register

• To rewrite the interrupt control register, do so at a point that does not generate the interrupt request for that register. If there is possibility of the interrupt request occur, rewrite the interrupt control register after the interrupt is disabled. The program examples are described as follow:

```
Example 1:
```

```
INT_SWITCH1:
    FCLR I ; Disable interrupts.
    AND.B #00h, 0055h ; Clear TA0IC int. priority level and int. request bit. NOP
```

NOP

FSET I ; Enable interrupts.

Example 2:

INT_SWITCH2:

FCLR I ; Disable interrupts.

AND.B #00h, 0055h ; Clear TA0IC int. priority level and int. request bit.

MOV.W MEM, R0 ; Dummy read. FSET I ; Enable interrupts.

Example 3:

INT_SWITCH3:

PUSHC FLG ; Push Flag register onto stack

FCLR I ; Disable interrupts.

AND.B #00h, 0055h ; Clear TA0IC int. priority level and int. request bit.

POPC FLG ; Enable interrupts.

The reason why two NOP instructions or dummy read are inserted before FSET I in Examples 1 and 2 is to prevent the interrupt enable flag I from being set before the interrupt control register is rewritten due to effects of the instruction queue.

 When a instruction to rewrite the interrupt control register is executed but the interrupt is disabled, the interrupt request bit is not set sometimes even if the interrupt request for that register has been generated. This will depend on the instruction. If this creates problems, use the below instructions to change the register.

Instructions: AND, OR, BCLR, BSET

Noise

- (1) Insert bypass capacitor between Vcc and Vss pin for noise and latch up countermeasure.
 - Insert bypass capacitor (about 0.1 μF) and connect short and wide line between Vcc and Vss lines.



GZZ-SH13-96B<02A0>

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30621MCM-XXXGP MASK ROM CONFIRMATION FORM

Mask ROM number	

	Date :	
	Section head signature	Supervisor signature
Receipt		

Note: Please complete all items marked * .

		Company		TEL		a)	е	Submitted by	Supervisor
*	Customer	name		()	ance	atur		
AIV.	Oustomer	Date issued	Date :			Issu	sign		

*1. Check sheet

Mitsubishi processes the mask files generated by the mask file generation utilities out of those held on the floppy disks you give in to us, and forms them into masks. Hence, we assume liability provided that there is any discrepancy between the contents of these mask files and the ROM data to be burned into products we produce. Check thoroughly the contents of the mask files you give in.

Prepare 3.5 inches 2HD (IBM format) floppy disks. And store only one mask file in a floppy disk.

Microcomputer type No. :	∐M30621MCM-XXXGP	
File code :		(hex)
Mask file name :		.MSK (alpha-numeric 8-digit)

*2. Mark specification

The mark specification differs according to the type of package. After entering the mark specification on the separate mark specification sheet (for each package), attach that sheet to this masking check sheet for submission to Mitsubishi.

For the M30621MCM-XXXGP, submit the 80P6S mark specification sheet.

***3.** Usage Conditions

For our reference when of testing our products, please reply to the following questions about the usage of the products you ordered.

(4) \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			
(1) Which kind of XIN-XOUT oscil	liation	circuit is used?	
Ceramic resonator		Quartz-crystal oscilla	ator
External clock input		Other ()
What frequency do not use?			
f(XIN) =	MHz		



GZZ-SH13-96B<02A0>

Mask ROM number

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30621MCM-XXXGP MASK ROM CONFIRMATION FORM

(2) Which kind of XCIN-XCOUT oscillation circuit is used?
Ceramic resonator Quartz-crystal oscillator
External clock input Other ()
What frequency do not use?
f(XCIN) = kHz
(3) Which operating supply voltage do you use? (Circle the operating voltage range of use)
2.2 2.4 2.6 2.7 2.8 2.9 3.0 3.1 3.2 3.3 3.4 3.5 3.6 3.7 3.8
(4) Which operating ambient temperature do you use? (Circle the operating temperature range of use)
-50 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90
(5) Do you use I ² C (Inter IC) bus function? ☐ Not use ☐ Use
(6) Do you use IE (Inter Equipment) bus function?
☐ Not use ☐ Use
Thank you cooperation.
*4. Special item (Indicate none if there is not specified item)



GZZ-SH13-49B<98A1>

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30625MGM-XXXGP MASK ROM CONFIRMATION FORM

Mask ROM number
Mask ROM number

	Date :	
	Section head	Supervisor
<u>i</u>	signature	signature
Receipt		
že		
ш.		

Note: Please complete all items marked * .

		Company		TEL		a)	Φ	Submitted by	Supervisor
*	Customer	name		()	ance	atur		
40.	Customer	Date issued	Date :			nssı	sign		

*1. Check sheet

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Prepare 3.5 inches 2HD (IBM format) floppy disks. And store only one mask file in a floppy disk.

Microcomputer type No. :	☐M30625MGM-XXXGP	
File code :		(hex)
Mask file name :		.MSK (alpha-numeric 8-digit)

*2. Mark specification

The mark specification differs according to the type of package. After entering the mark specification on the separate mark specification sheet (for each package), attach that sheet to this masking check sheet for submission to Mitsubishi.

For the M30625MGM-XXXGP, submit the 80P6S mark specification sheet.

***3.** Usage Conditions

For our reference when of testing our products, please reply to the following questions about the usage of the products you ordered.

(1) Which kind of XIN-XOUT oscillation	circuit is used?	
Ceramic resonator	Quartz-crystal osci	llator
External clock input	Other ()
What frequency do not use?		
f(XIN) = MHz		



GZZ-SH13-49B<98A1>

Mask ROM number

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30625MGM-XXXGP MASK ROM CONFIRMATION FORM

(2) Which kind of XCIN-XCOUT oscillation circuit is used?
Ceramic resonator Quartz-crystal oscillator
External clock input Other ()
What frequency do not use?
f(XCIN) = kHz
(3) Which operating supply voltage do you use?
(Circle the operating voltage range of use)
2.2 2.4 2.6 2.7 2.8 2.9 3.0 3.1 3.2 3.3 3.4 3.5 3.6 3.7 3.8
(4) Which operating ambient temperature do you use? (Circle the operating temperature range of use)
-50 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90
(5) Do you use I ² C (Inter IC) bus function? ☐ Not use ☐ Use
(6) Do you use IE (Inter Equipment) bus function?
☐ Not use ☐ Use
Thank you cooperation.
*4. Special item (Indicate none if there is not specified item)



M16C/62M(80-PIN VERSION) GROUP DATA SHEET

Rev. Date Description Page Summary A1 02/04/02 5 Figure 1.1.3 is revised. Table 1.1.2 is revised.	
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Renesas Technology Corp.

Nippon Bldg.,6-2,Otemachi 2-chome,Chiyoda-ku,Tokyo,100-0004 Japan

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